UF28100H



RF Power MOSFET Transistor 100W, 100-500 MHz, 28V

M/A-COM Products Released - Ver 08.07

Features

- N-channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- High saturated output power
- Lower noise figure than competitive devices
- RoHS Compliant

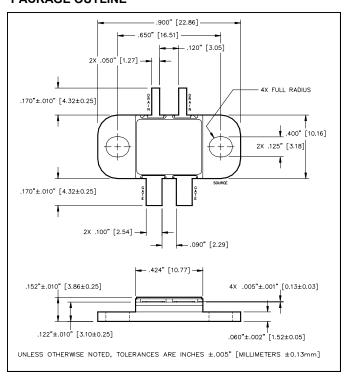
ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	20	V
Drain-Source Current	I _{DS}	12*	Α
Power Dissipation	P_D	250	W
Junction Temperature	T_J	200	°C
Storage Temperature	T_{STG}	-55 to +150	°C
Thermal Resistance	θ_{JC}	0.7	°C/W

TYPICAL DEVICE IMPEDANCES

F (MHz)	Z _{IN} (Ω)	Z _{LOAD} (Ω)			
100	4.5-j6.0	14.5+j0.5			
300	2.25-j1.75	7.5j1.0			
500	1.5+j5.5	3.5+j3.5			
V_{DD} =28V, I_{DQ} =600 Ma, P_{OUT} =100.0 W					

PACKAGE OUTLINE



 Z_{IN} is the series equivalent input impedance of the device from gate to gate.

Z_{LOAD} is the optimum series equivalent load impedance as measured from drain

ELECTRICAL CHARACTERISTICS AT 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	65	-	V	V _{GS} = 0.0 V , I _{DS} = 15.0 mA
Drain-Source Leakage Current	I _{DSS}	-	3.0	mA	$V_{GS} = 28.0 \text{ V}$, $V_{GS} = 0.0 \text{ V}$
Gate-Source Leakage Current	I _{GSS}	-	3.0	μA	V _{GS} = 20.0 V , V _{DS} = 0.0 V
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	V _{DS} = 10.0 V , I _{DS} = 300.0 mA
Forward Transconductance	G _M	1.5	-	S	V_{DS} = 10.0 V , I_{DS} 3000.0 mA , Δ V_{GS} = 1.0V, 80 μ s Pulse
Input Capacitance	C _{ISS}	-	135	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Output Capacitance	Coss	-	90	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Reverse Capacitance	C _{RSS}	-	24	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Power Gain	G _P	10	-	dB	V _{DD} = 28.0 V, I _{DQ} = 600.0 mA, P _{OUT} = 100.0 W F =500 MHz
Drain Efficiency	η _D	50	-	%	V _{DD} = 28.0 V, I _{DQ} = 600.0 mA, P _{OUT} = 100.0 W F =500 MHz
Return Loss	R _L	10	-	dB	V_{DD} = 28.0 V, I_{DQ} = 600.0 mA, P_{OUT} = 100.0 W F =500 MHz
Load Mismatch Tolerance	VSWR-T	-	30:1	-	V_{DD} = 28.0 V, I_{DQ} = 600.0 mA, P_{OUT} = 100.0 W F =500 MHz

^{*}Per side

North America Tel: 800.366.2266 / Fax: 978.366.2266

[•] Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300

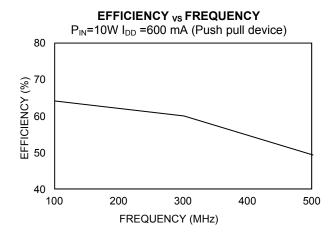
Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.

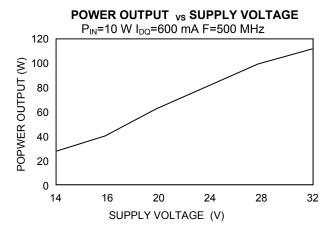


RF Power MOSFET Transistor 100W, 100-500 MHz, 28V

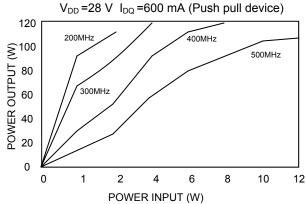
M/A-COM Products Released - Ver 08.07

Typical Broadband Performance Curves





POWER OUTPUT vs POWER INPUT



- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.

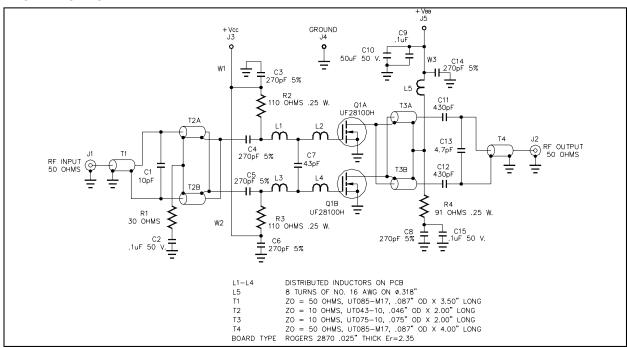
UF28100H



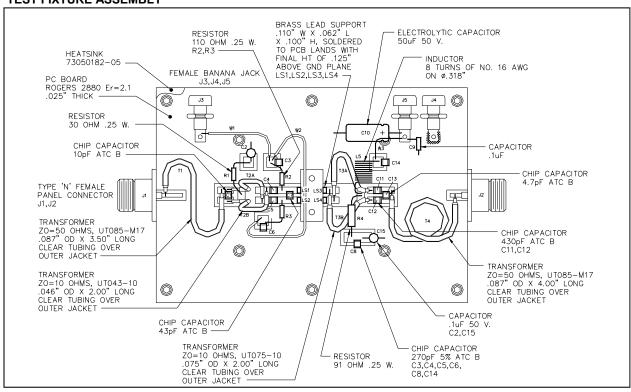
RF Power MOSFET Transistor 100W, 100-500 MHz, 28V

M/A-COM Products Released - Ver 08.07

TEST FIXTURE SCHEMATIC



TEST FIXTURE ASSEMBLY



- North America Tel: 800.366.2266 / Fax: 978.366.2266
- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.